

AMENDMENT TO THE CLAIMS

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1-10. (Canceled)

11. (Currently amended) An epitaxial growth method comprising:
growing an epitaxial layer on a layered substrate which exhibits bowing so as to flatten
said bowed layered substrate, wherein the layered substrate has at least two layers,
wherein at least two of the layers have different thermal coefficients.

12. (Previously presented) The epitaxial growth method of claim 11 further comprising
the step of selective etching a portion of the epitaxial layer.

13. (Original) The epitaxial growth method of claim 11 wherein the epitaxial layer
comprises a III-V nitrides alloy and the material of the top layer of the layered substrate
is selected from the group consisting of sapphire, silicon, silicon carbide, zinc oxide,
gallium arsenide, gallium phosphide, indium phosphide, LiGaO_2 , and LiAlO_2 .

14. (Original) The epitaxial growth method of claim 11 wherein the epitaxial layer
comprises a III-V nitrides alloy and the substrate is selected from the group consisting of
sapphire on silicon, sapphire on a III-V nitrides alloy, sapphire on zinc oxide, and
sapphire on silicon carbide.

15. (Previously presented) An epitaxial growth method comprising:
directly heating a substrate by a radiation source without using any heat sink
material;